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Always: A System for Wafer Yield Analysis

Report and User's Manual

by

J. Pineda de Gyvez

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ABSTRACT

An interactive environment for the analysis of yield information needed on modern integrated circuit manufacturing lines is presented. The system is able to quantify wafer yields, yield variations between wafers and within the wafers themselves, yields of wafer batches, yield variations between batches, to identify clusters in wafers and or in lots, and is also able to predict wafer yields via simple simulation tools. The analysis technique investigates the effect of correlated and uncorrelated sources of yield loss. Such information can be used to study the changes in the technological process. Graphical displays in the form of wafer maps are used to represent the spatial distribution of dice in the wafer. Facilities such as radial and angular distribution analyses, among others, are provided to examine data, and hypothetical wafer maps are created to visualise and predict simulated wafer yields.

Pineda de Gyvez, J.

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Author's address:

Automatic System Design Group,
Faculty of Electrical Engineering,
Eindhoven University of Technology,
P.O. Box 513,
5600 MB EINDHOVEN,
The Netherlands

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ALWAYS
Report

1. INTRODUCTION.

The ever growing complexity of very large scale integrated circuit chips demands tools to analyse the spatial yield distribution of wafers and to relate this information to the particular layout for fault prediction [13], [14], [17], [24], [26] and design yield estimation. Increasing the levels of semiconductor integration to larger chips with more and more transistors addresses topics such as the yield associated with individual process steps like etching, metallisation, etc. or the spatial distribution of random and systematic sources of yield loss [27], [28], [29].

The actual production wafers are an excellent source of information available at minimum effort and low cost that reliably reflect the limiting factors existing in the technology process. Interaction with these factors can be aided by analysing the wafer maps where functional, nonfunctional and partially functional regions can easily be observed.

Better circuit designs and yield improvements can be achieved by understanding the properties of complete wafers and by redirecting these results exactly to the process and design stages where they belong.

It is then necessary a tool to manage the enormous amount of data coming from the manufacturing lines and to condense it in useful information for the process engineer, the layout designer, the quality engineer, etc. or for whom yield prediction and estimation are very important issues for the IC design and process development.

It is well known that the local yield varies from wafer to wafer and that by examining batches of wafers it is possible to correlate non functional circuits and their contributions to yield loss. Sometimes it is desirable not only to analyse data but also to simulate the effect of density variations in a wafer and between wafers, or to exercise new yield models and compare their results to real data.

For these and more reasons, the creation of a user friendly interactive environment is imperative. This research is concerned with the development of the *Wafer Yield Editor* ALWAYS (AnaLiser of WAfer YieldS). ALWAYS is a menu oriented system designed to analyse spatial distributions of wafers. Graphical representations in the form of wafer maps, curves, and charts are used extensively for user interface. Flexibility to create wafer masks, wafers, and chips of different dimensions, as well as several miscellaneous tools such as hardcopy, overlapping of extracted wafer maps, etc., are provided. Simulation of wafer maps and yield vs. area predictions are also available. And finally, data is read and stored in a very simple database structure.

All the algorithms through this report are shown in a C like syntax.

2. INPUT DATA AND DATABASE DESCRIPTION.

The starting data is a set of wafer maps of working and nonworking circuits of individual wafers produced from the process of interest. The data gathered for the analysis can be collected from electrical sort systems or by optically decoding the ink dot pattern placed on the wafers during the sort procedure. This allows automatic printout of the maps in an easy form for further manipulation of data.

Input data to the yield editor consists of all the die positions and their status, good or bad, of each wafer in each lot for each project. We define a set of wafers as a *lot* and a set of *lots* as a *project*. This classification allows us to hierarchise the information. Hence, the database description follows a tree structure where the parent is the product itself, the children represent each one of the lots of the product, and the grandchildren represent the individual wafers for each lot, see Fig. 1. Since the information flows from grandparent to grandchildren a double linked structure is unnecessary and thus we only have single connected lists, this saves some memory space in defining extra pointers and simplifies the code since only one link has to be updated for deleting or inserting elements in the list.

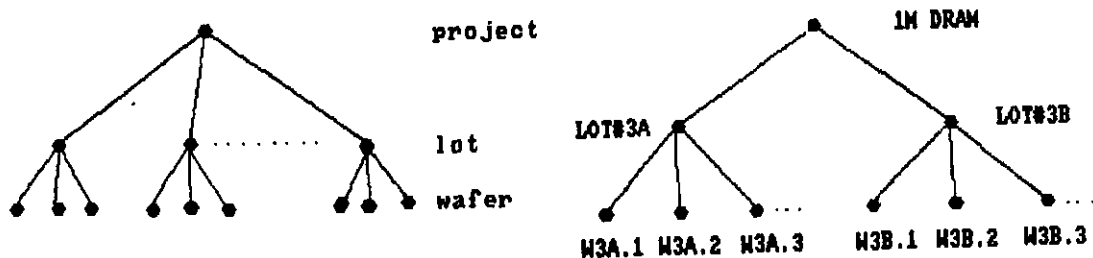


Figure 1. (a) The information is hierarchised in a tree structure. (b) An example.

Internally we place the dice in a square matrix that we call the mask. The mask represents the photolithographic mask of the technological process. Once that the projects, lots and wafers for the analysis are selected it is easy to generate a general matrix which contains the history of all the wafers implied. Since the mask can be of arbitrary size, bigger or smaller than the wafer, it is then necessary to prevent writing wrong information, this is done by checking if the die lays inside of the wafer. The following routine shows how the tree structure is traversed in order to obtain information from each wafer.

```
generate_working_wafer()
{
    while( project_pointer != NULL ) {
        while ( lot_pointer != NULL ) {
            while ( wafer_pointer != NULL ) {
                for ( x = 0; x < total_dice_in_x; x++ ) {
                    for ( y = 0; y < total_dice_in_y; y++ ) {
                        if ( die_in_wafer(x,y) ) {
                            if ( wafer_pointer->status[x][y] == GOOD )
                                composite_wafer[x][y] += 1;
                        }
                    }
                }
                wafer_pointer = wafer_pointer->next;
            }
        }
    }
}
```



```
        lot_pointer = lot_pointer->next;
    }
    project_ptr = project_ptr->next;
}
}
```

It is possible to make analysis between wafers of the same or different lots, between lots of the same or different projects, and between different projects. Notice that the concept of project is very flexible, it can mean i.e. a memory chip, a test structure, or simply the same memory chip processed with a new equipment or new chemicals in which it was desirable to make a difference between the new and the old process.

Input data does not necessary have to represent the absolute die coordinates in the wafer. Assume for a moment that a test chip contains a monitor to detect up to four multiple spot defects. If one wants more accuracy or simply wants to reflect the number of defects it is possible to subdivide the test chip in four, where each subdivision represents a defect. The data could be now the coordinates of each one of the new *subdice* and its status, let us say, good for a defect present and bad for a defect not present, see Fig. 2.

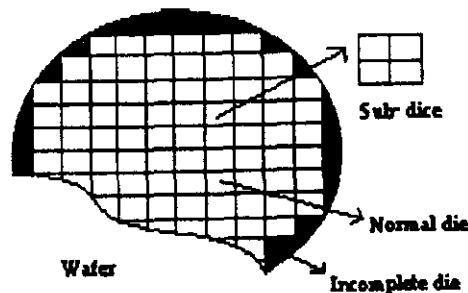


Figure 2. Dice configuration in the wafer.

Then, when a radial distribution analysis is executed, it will mean the radial defect density instead of the original monitor density, and furthermore, accurate data as the number of defects will also be obtained.

The flexibility in the database structure, as well as in the input data permits the user to cope with almost any situation in spatial yield analysis. The only limits, thus, are restricted to the user itself and to the type of information available for the analysis. A well known method of obtaining significant information is by using test structures [22], [23] for process monitoring [10]. This implies that different types of information are used by different kind of users. When the parameters supplied to the editor are, i.e. linewidths, resistivity, oxide thickness, etc., then the production stage can have impact on yield through a correct analysis procedure and an appropriate corrective action. On the other hand, if the parameters are defect distributions, distribution of opens and shorts in different layers, distribution of good and bad chips, etc., then the design engineering stage will benefit itself doing analysis through the yield editor.

3. WAFER SIZE AND DIE ASSIGNMENTS.

The wafer size and die shape are user entries which can be modified at any time. Dice are placed on an imaginary square which represents the photolithographic *mask* of the fabrication process. The shape of the dice can take the form of a rectangle of any size, and the center of the mask is used as a reference point to center the wafer frame, see Fig. 2.

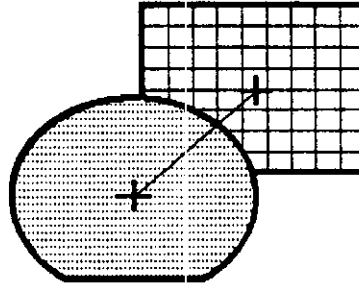


Figure 3. Wafer position with respect to the mask.

The placement of dice in the mask goes from left to right and from bottom to top, as shown in Fig. 4. This is important since dice are clipped to the wafer and partial dice are discarded. The size of the mask is also adjustable to any value.

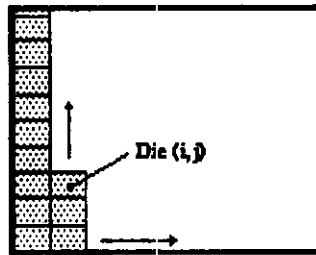


Figure 4. Die arrangement in the mask.

Examining whether a die is in or out of the wafer is a tedious algorithm because it is necessary to check if the four corners of the die lay inside of the wafer. The procedure that we employ calculates the distance from each corner to the center of the mask, remember that the wafer is centered with respect to the center of the mask, and then evaluates if all these distances are less or equal than the wafer radius. The input parameters to this routine are the coordinates of the die with respect to the left corner of the mask. To transform the coordinates to distances we simply multiply them by the size of the die in the x and y directions. For simplicity the flat side of the wafer is approximated to $0.04R$ [15], where R is the wafer radius. The final routine looks as follows

```
die_in_wafer(i,j)
{
    x                = die_size_x * i;
    y                = die_size_y * j;

    /* out of the mask ??? */
    if ( x + die_size_x > mask_size || y + die_size_y > mask_size )
        return(OUTSIDE);
}
```

```
flat          = 0.04 * wafer_radius;
left_bottom_x = mask_center - ( x + displace_x );
left_bottom_y = mask_center - ( y + displace_y );
left_top_x    = left_bottom_x;
left_top_y    = left_bottom_y - die_size_y ;
right_bottom_x = left_bottom_x - die_size_x ;
right_bottom_y = left_bottom_y;
right_top_x    = right_bottom_x;
right_top_y    = left_top_y;

radius_lb     =
sqrt (left_bottom_x * left_bottom_x + left_bottom_y * left_bottom_y );
radius_lt     =
sqrt (left_top_x * left_top_x + left_top_y * left_top_y );
radius_rb     =
sqrt (right_bottom_x * right_bottom_x + right_bottom_y * right_bottom_y);
radius_rt     =
sqrt (right_top_x * right_top_x + right_top_y * right_top_y );
/* below the flat ??? */
if ( left_bottom_y > 0 && left_bottom_y > (wafer_radius - flat ) )
    return(OUTSIDE);
/* in the wafer ??? .... */
if ( radius_lb <= wafer_radius && radius_lt <= wafer_radius )
    if ( radius_rb <= wafer_radius && radius_rt <= wafer_radius )
        return( INSIDE );
return ( OUTSIDE );
}
```

Some variables are redundant but they were left for a matter of clarity.

Fixing the wafer's center with the center of the mask does not always achieve the maximum number of dice in the wafer, or simply it does not look like the "real life" wafer. However, the availability of a mask with all the dice allows to "move" the wafer frame in order to obtain the "real life" dice configuration. Thus the wafer can be shifted up, down, left or right through the mask at user's will. The amount of shifting is specified in `displace_x` and `displace_y` in the previous routine.

In addition to the normal dice it is also possible to specify *dead dice*. The locations of these dice are considered *dead* and are not taken in account for analyses or simulations. In production wafers they represent the test sites for instance.

It is also possible to obtain the maximum number of dice in the wafer according to [15], see Fig. 5. In our case the parameters G and H are made to be less or equal to the size of the die in the horizontal and vertical directions, respectively. The following routine finds the displacement of the wafer with respect to the mask center in order to obtain the maximum number of dice. Notice that this is a very expensive routine since it has to iterate $die_size_x * die_size_y * i * j$ times before it can output correct results. The accuracy of the routine depends on the delta values, the smaller they are the more accurate results we obtain.

```
maximum()
{
    dice = max = max_x = max_y = 0;
    displace_x = displace_y = 0;
```

```
for ( displace_x = 0; displace_x < die_size_x; displace_x += delta_x ) {  
    for ( displace_y = 0; displace_y < die_size_y; displace_y += delta_y ) {  
        for ( i = 0; i < number_dice_in_x; i++ ) {  
            for ( j = 0; j < number_dice_in_y; j++ ) {  
                if ( die_in_wafer( i, j ) )  
                    dice++;  
            }  
        }  
        if ( dice > max ) {  
            max = dice;  
            max_x = displace_x;  
            max_y = displace_y;  
        }  
        dice = 0;  
    }  
}
```

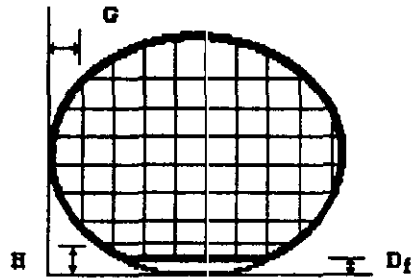


Figure 5. Wafer displacement from the center of the mask.

The final configuration of the wafer, i. e. the size, the dice's size, etc., is considered as the prototype wafer and will be used in the analyses and simulations.

4. THE MAP AND DISTRIBUTION ANALYSES.

The analysis is based on cumulative results by doing the Boolean And on a set of wafers. The result is a composite wafer map which contains the cumulative yield by site location as shown in Fig. 6. This methodology and its benefits were already reported for a specific application in [16] and for a spatial analysis in [19]. We extend it by considering not only the individual wafer variations but also by taking in account the lot and project variations of the product.

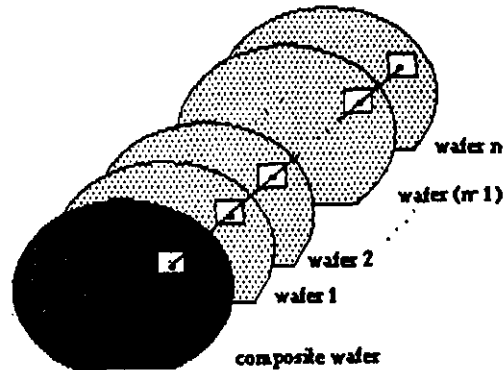


Figure 5. The Boolean And of wafers.

In Fig. 7 we can see the typical flow of an analysis. This kind of wafer convolution allows also to consider the mean and standard deviations between lots and between projects, a well known problem [11]. Furthermore, the methodology exploits the fact that wafers have statistically dependent yield patterns for certain processing steps, and also that wafer yields are usually correlated when processed in the same lot or under similar conditions.

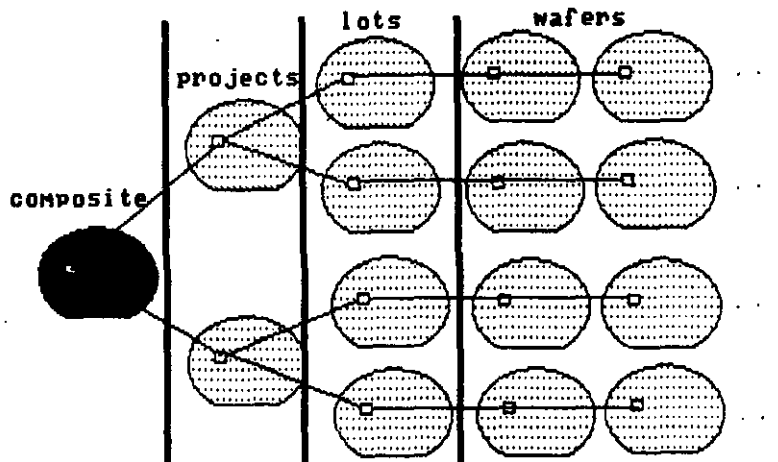


Figure 7. The convolution of wafers in a typical analysis

The within wafer yield variations are inspected by using the concept of *site yield*. A site yield shows how many times in the complete set of wafers involved in the analysis a particular die

accomplished a function. For instance, if our analysis consists of a lot of ten wafers and one die in the composite wafer was only five times good, then its functional site yield is of 50%. Thus we can write the site yield as

$$Y_{site} = \frac{F_{site}}{N_A} \quad (1)$$

where F_{site} is the site frequency, in other words the number of times that the die was projected, and N_A is the number of wafers involved in the analysis.

It is obvious that by using this approach we can account for wafer to wafer, and lot to lot variations, as well as regional variations in wafers.

ALWAYS can execute two kinds of analysis on data. One is called the *map analysis* and the other the *distribution analysis*. The map analysis displays the composite wafer map with the projected dice that accomplished the function, and its purpose is mainly intended to see the correlated spatial behaviour of the input data. The distribution analysis, on the other hand, quantifies the behaviour of the input data by showing the curves of different types of distributions of the final composite wafer map.

The map analysis that ALWAYS can carry on are:

- + **Functional Map.** The functional map shows all the die locations which were good all the time in the whole set of wafers selected for the analysis. Additionally, the correlated mean and standard deviations between lots and projects is also evaluated for good dice. From the practical point of view this map is useful in determining which are the most correlated dice in a wafer in order to assure a minimum wafer yield for evaluating product costs, for instance.
- + **Zero Map.** The zero map shows all the die locations which were bad all the time in the whole set of wafers selected for the analysis. As with the functional map the mean and standard deviations are evaluated but this time is for bad locations. This map shows immediately which are the dice detractors and major contributors to yield loss, one can also observe from this map the least correlated regions in a wafer.
- + **Up-range Map.** This map shows all the die locations which showed a specific yield, or above it, for the whole set of wafers. The correlated statistics are also evaluated for lots and projects, i.e. the specified yield is also looked up in every lot and in every project. The specific yield is a user entry. We can use this map, for instance, to investigate the general correlation of a specific process step along the entire lot. Let's say that the input data were process parameters, like the V_t of depletion transistors, then by asking to show the 50% site yield, or more, we can infer about the uniformity of the ion implantation process step, for instance.
- + **Low-range map.** This analysis shows the locations with a specific site yield or less. In certain form this map is the complement of the previous one. An example of its use is when the input data are defect sizes, i. e. a die is good if the defect size measured for that location is of a predefined value, otherwise it is bad. We can organise the data in such a way that one project contains information of defects of size x and another project of defects of size y , and so on. Thus, if we select only one project and we ask for the locations where the specific site yield is 50% or less, we mean that we want to know the correlation of defects along the whole set of wafers involved in the project. The result could be interpreted as an index of how many times defects of the same size showed to be clustered in the same place in half, or less, of the total wafers involved in the analysis.
- + **History map.** This analysis shows numerically the yield of each die location for the whole set of wafers. The uncorrelated analysis showing the mean and standard deviations between

wafers, lots, and projects is displayed here. This numerical information is useful to quantify each site yield of the composite wafer.

- + **Informative map.** This is a contour informative map, it shows the average and the above and below average site yield of the dice. Zero yield locations are distinguished from the rest of the dice. This analysis allows to visualise the uniform distribution of the type of input data in question. For our previous example of Vts this map shows the scanning uniformity of the ion beam of the ion implanter, if there were doubts about the equipment, or the effectiveness of the mask employed for this process step. For our example of defect sizes, this maps shows the distribution of defects of a specific size along the wafer and through the entire lot.
- + **Cluster map.** In this analysis the user is asked to specify the number of elements that define a cluster and the site yield for the dice. The resulting map shows the clusters according to the previous specifications. Statistics such as the numbers of clusters and the number of clustered dice are reported.

Lets investigate now into a bit more of detail the generation of the map analyses. The next piece of code shows how do we find the functional map, however, this routine can easily be extended to find the other map analyses. We make use of the fact that the information is stored in a matrix, thus we first check whether the element in turn of the matrix, in other words the die, lays inside of the wafer and if it does whether it accomplished a hundred per cent yield. If both conditions are satisfied we can proceed to project the die by drawing it and also to update the computation of the functional yield.

```
functional_map()
{
    for ( x = 0; x < total_dice_in_x; x++ ) {
        for ( y = 0; y < total_dice_in_y; y++ ) {
            if ( die_in_wafer(x,y) ) {
                if ( composite_wafer[x][y] == SITE_YIELD ) {
                    draw_die(x,y);
                    functional_yield++;
                }
            }
        }
    }
    functional_yield = functional_yield / total_number_of_dice;
}
```

In order to be able to find clusters in the wafer it is necessary to define clearly what a cluster means. We define a cluster as a number of contiguous dice that have the same site yield. Thus, clustered elements can be in the horizontal, vertical or even diagonal directions with respect to a "seed element". The seed element is the die which was taken as a reference for the search of contiguous dice. The routine that implements this search uses the principle of the "depth search" algorithm.

The main idea behind this algorithm is to take one die that has the cluster yield specified and then look if its neighbours also have the specified yield. Since the number of neighbours and their directions is unknown it is necessary to check for the neighbours of the neighbours and then for the neighbours of the neighbours of the neighbours, and so on. At first glance we see that this routine is suited for recursivity. Next, to determine whether the dice found form a cluster or not we simply check against the number of elements that make up a cluster. This parameter is a user entry, thus we can find clusters of one, two, or more elements. The next routine finds the dice that

have the same site yield and marks them in the "cluster wafer". This routine is part of a main one where first the seed element is set and later it is investigated if the marked dice form a cluster by comparing the number of cluster elements with the minimum number of elements.

```
find_clusters(x, y)
int x, y;
{
    /* These are the cardinal points, i.e. NW is north west,
       NO north, etc.
       NW, NO, NE, WE, EA, SW, SO, SE, SEED */
    int xoff[9] = { -1, 0, 1, -1, 1, -1, 0, 1, 0};
    int yoff[9] = { -1, -1, -1, 0, 0, 1, 1, 1, 0};

    cluster_map[x][y] = mark;
    cluster_elements++;
    for (next = 0; next < 8; next++) {
        neighbour_x = x + xoff[next];
        neighbour_y = y + yoff[next];
        if (neighbour_x < 0)
            neighbour_x = 0;
        else
            if (neighbour_x > total_dice_in_x)
                neighbour_x = total_dice_in_x;
        if (neighbour_y < 0)
            neighbour_y = 0;
        else
            if (neighbour_y > total_dice_in_y)
                neighbour_y = total_dice_in_y;
        if ((die_in_wafer(neighbour_x, neighbour_y))
            if (composite_wafer[neighbour_x][neighbour_y] == CLUSTER_YIELD)
                if (cluster_map[neighbour_x][neighbour_y] != mark)
                    find_clusters(neighbour_x, neighbour_y);
    }
}
```

In order to account for the different density variations in the wafer, and to quantify the yield loss we provide a radial distribution inspection [1], [4], [8] of the composite wafer. Furthermore, the combination of the radial analysis with an angular analysis [7] will facilitate us to observe the behaviour of clustering. Another important source of information is a site yield frequency distribution [2] that tell us how many times in the whole set of wafers involved for the analysis a particular die site was projected. Through this analysis we can quantify the die correlation of wafers and have a defined idea of correlated site yields. A natural consequence of the previous analysis is a cumulative frequency distribution analysis [9] which tells us about the overall behaviour of the whole set of wafers, for instance we can see immediately the probability of occurrence of each of the different site yields. Finally, an analysis which could not be omitted is the yield vs. area [3],[12].

In the radial and angular analysis the user is asked to specify the site yield which is going to be looked for. This adds flexibility to the analysis, since in this form we can obtain a set of different curves for different site yields. One example that makes use of this idea is when we want to analyse the frequency of occurrence of defects in different regions of the wafer. So, we can obtain radial or angular distributions for 0, 1, 2, or N defects and each analysis independent of the other.

In the yield vs. area analysis the user is also asked to specify the site yield. The kind of benefits that we can obtain from this feature are i.e. the number of defects per area in order to classify clusters [5],[6] or simply the "traditional" yield vs. area curve.

A routine of interest is the generation of the radial distribution. The radial plots are made using concentric rings of constant area to determine the site yield at a distance r from the center of the wafer. If r_1 is the inner radius and r_2 is the outer radius of the ring, the area is kept constant by taking r_2 as

$$A = \pi(r_2^2 - r_1^2)$$

$$r_2 = \sqrt{\frac{A}{\pi} + r_1^2}$$

Instead of incrementing the angle in one degree we maximise the angle by obtaining the arc sine of the hypotenuse of the die and the radius of the wafer. This will give us the minimum incremental angle for a full coverage of dice along the scanning line. We do the same for the radial increment, in this case we take the minimum value between the size of the die in the vertical and horizontal directions. Since we deal with die sites, it is necessary to find the coordinates of any die for any given x and y vector components of the changing radius. This is carried on in the `find_die_at_radius()` function where the vector components are converted to the corresponding die coordinates. Finally, to avoid counting a die which was already considered within the previous angle and or radius, we simply mark it and skip it if necessary.

The next routine applies these concepts.

```
radial_distribution()
{
    area = PI * (wafer_radius) * (wafer_radius) / 10.0;
    r1 = 0;
    r2 = sqrt ( area / PI );
    squared_x      = die_size_in_x * die_size_in_x;
    squared_y      = die_size_in_y * die_size_in_y;
    die_size       = sqrt ( squared_x + squared_y );
    delta_theta    = asin ( die_size / wafer_radius );
    delta_radius   = MIN( die_size_in_x, die_size_in_y );
    do {
        radial_yield = elements_found = 0;
        for ( theta = 0; theta < 2 * PI; theta += delta_theta ) {
            for ( radius = r1; radius <= r2; radius += delta_radius ) {
                x = radius * cos( theta );
                y = radius * sin( theta );
                find_die_at_radius( &x,&y );
                if ( radial_mark[x][y] == FALSE ) {
                    radial_mark[x][y] = TRUE;
                    elements_found++;
                    if ( composite_wafer[x][y] == SITE_YIELD )
                        radial_yield++;
                }
            }
        }
        plot ( r2, radial_yield / elements_found );
        r1 = r2;
        r2 = sqrt ( area / PI + ( r1 * r1 ) );
    } while ( r2 <= wafer_radius );
}
```

5. THE STATISTICS.

The wafer maps standing alone are a good means to display the regional distribution of the input data on wafers. Although they are a good tool they are usually not enough. One is generally interested in quantifying the results in order to make conclusions of the analysis, i.e. to know the yield of good dice, the variations of good dice between wafers, etc. It is thus necessary to count with a minimum set of statistical information as to make inferences about the wafer or set of wafers in analysis.

The first information is the yield of the function, i.e. the yield of good dice, the yield of bad dice, etc. This yield is evaluated as

$$Y_F = \frac{N_f}{N_c} \quad (2)$$

where N_f is the number of dice that accomplished the function and N_c is the total number of dice of the composite wafer, excluding the dead dice. It is also of interest to find how did the function performed in each lot and in each project. Thus, for each function we give information about the mean yield per lot, and per project, with their corresponding variances. Each partial yield is an independent random variable and altogether constitute a random sample for whose mean x_p and variance s_p^2 are given according to [25] by:

$$x_p = \frac{1}{N} \sum_{i=1}^{i=N} Y_i \quad (3)$$

$$s_p^2 = \frac{1}{N-1} \sum_{i=1}^{i=N} (Y_i - x_p)^2 \quad (4)$$

where Y_i represents each partial yield and N is the size of the sample. These two quantities give an idea of the performance of the function per lot or per project. Furthermore, a 95% degree of confidence of the mean yield value is evaluated. If x_p and s_p are the values of the mean and standard deviation of the sample of size N , then the $(1 - \alpha)100\%$ confidence interval for the population mean γ is:

$$x_p - t_{\frac{\alpha}{2}, N-1} \frac{s_p}{\sqrt{N}} < \gamma < x_p + t_{\frac{\alpha}{2}, N-1} \frac{s_p}{\sqrt{N}} \quad (5)$$

This means that if we had more lots, or projects, we could assert with $(1 - \alpha)100\%$ degree of confidence that the true average lot yield is between the two boundaries.

Since the methodology exploits correlation of wafers we also provide an expected value of dice and its standard deviation. This expected value is the mean of the distribution of dice that accomplished a specific function. If z is a random variable representing the site frequency, in other words the number of times that a die can accomplish the function, and $f(z)$ is the number of dice that exhibit the site frequency in the composite wafer, then the mean is given by

$$\mu = \sum_{z=1}^{z=N_{wafer}} z \frac{f(z)}{N_{dice}} \quad (6)$$

where N_{dice} is the total number of dice in the wafer, and N_{wafer} is the number of wafers in the analysis. The standard deviation is given by

$$\sigma = \left(\sum_{z=0}^{z=N_{wafer}} (z - \mu)^2 \frac{f(z)}{N_{dice}} \right)^{\frac{1}{2}} \quad (7)$$

The statistics that we showed so far are for correlated functions. The history map has a set of uncorrelated statistics. First, the yield here is evaluated as

$$Y_U = \frac{N_g}{N_t} \quad (8)$$

where N_g is the total number of dice that were good during the analysis, and N_t represents the total number of dice in the analysis.

The variation between wafers is inspected by evaluating the yield of good dice in each wafer. Then the mean yield x_w and variance s_w^2 for wafers is given by

$$x_w = \frac{1}{N} \sum_{i=1}^{i=N} Y_i \quad (9)$$

$$s_w^2 = \frac{1}{N-1} \sum_{i=1}^{i=N} (Y_i - x_w)^2 \quad (10)$$

where Y_i is the yield of each wafer and N is the total number of wafers involved in the analysis. The uncorrelated mean yield and variance for lots and projects is also evaluated as

$$x = \frac{1}{N} \sum_{i=1}^{i=N} Y_i \quad (11)$$

$$s^2 = \frac{1}{N-1} \sum_{i=1}^{i=N} (Y_i - x)^2 \quad (12)$$

where Y_i represents the yield of good dice in the lot or project, and N the total number of lots or projects. Finally, the mean of the distribution of working chips and its standard deviation is evaluated as

$$\mu = \sum_{x=1}^{x=N_{\text{wafer}}} x \frac{f(x)}{N_{\text{dice}}} \quad (13)$$

$$\sigma = \left(\sum_{x=1}^{x=N_{\text{wafer}}} (x - \mu)^2 \frac{f(x)}{N_{\text{dice}}} \right)^{\frac{1}{2}} \quad (14)$$

where x represents the site frequency of a die and $f(x)$ represents the number of dice that exhibit the site frequency.

Cluster statistics are considered in a similar way. First we find the number of clusters C and their total number of elements G in the composite wafer. We also evaluate the mean number of clusters x_c and the mean number of clustered elements x_G , with their respective variances s_c^2 s_G^2 , per lot and per project. This is done as follows

$$x_c = \frac{1}{N} \sum_{i=1}^{i=N} C_i \quad (15)$$

$$s_c^2 = \frac{1}{N-1} \sum_{i=1}^{i=N} (C_i - x_c)^2 \quad (16)$$

$$x_G = \frac{1}{N} \sum_{i=1}^{i=N} G_i \quad (17)$$

$$s_G^2 = \frac{1}{N-1} \sum_{i=1}^{i=N} (G_i - x_G)^2 \quad (18)$$

where C_i represents the number of clusters G_i the number of clustered elements and N the size of the sample, i.e. the number of lots or projects. A 95% confidence interval for the mean number of clusters and of clustered elements is also evaluated.

This minimum set of statistics allows us to inspect the variations between wafers, lots and projects.

6. SIMULATIONS.

ALWAYS provides two kinds of simulations. One is the evaluation of the yield vs. area and the other is the creation of wafer maps. The yield vs. area is evaluated using a distribution of the number of defects per chip, and its formula is given according to [12] as:

$$Y = [AD(\frac{\sigma}{\mu})^2 + 1] \cdot (\frac{\mu}{\sigma})^2 \quad (19)$$

where A is the area of the die in the prototype wafer, D is the average defect density, and $\frac{\sigma}{\mu}$ the coefficient of the defect density variation. In this simulation the user is able to give the mean and the standard deviations as input data or, to create a file containing the description of the distribution to be used, or can draw the distribution online.

The wafer map simulation is for one lot. The number of wafers in the lot is a user entry, and the characteristics of the wafer correspond to the prototype wafer. The input data to simulate wafer maps consists of the relative radial distribution of site yields, expressed as follows

$$Y_R = \frac{N_g}{N_R} \quad (20)$$

where N_g is the number of good dice at radius R and N_R is the total number of dice at radius R . It is clear that the within wafer variations are considered with a radial distribution. Now, in order to consider the variations between wafers, one has to bear in mind that some wafers exhibit a higher radial yield and some a lower. Therefore, the input data consists in fact of two radial distributions, one for the upper bound and the other for the lower bound. Thus the regional variation of the simulated wafers lays between these two limits as

$$\delta = Y_{R_u} - Y_{R_l} \quad (21)$$

where Y_{R_u} is the upper radial yield and Y_{R_l} is the lower radial yield, both at radius R . Hence, the simulation is left to the task of generating a random number of good dice for whose relative radial yield at wafer radius R lays between these two boundaries.

The next routine applies the former idea. The input parameters to the routine are the partial radius and the number of dice at that radius. This routine forms part of a main loop in which the the partial radius is incremented from zero to the wafer radius and that for each partial radius the corresponding number of dice is found.

simulate_radial_dice(radius,number_dice)

```
{
    if ( upper_yield(radius) < lower_yield(radius) ) {
        error();
        return(FALSE);
    }
    good_dice = upper_yield(radius) * number_dice;
    bias      = good_dice - lower_yield(radius) * number_dice;

    /* generate the number of good dice randomly */
    random_dice(number_dice,good_dice,bias);

    /* place the generated good dice */
    random_placement(radius,number_dice);
    return(TRUE);
}
```

}

As with the yield vs. area simulations the distributions can be given in a file or can be drawn directly on screen. After the wafers are created it is possible to examine each one of them and also to perform any of the map analyses on the composite simulated wafer. In these simulated maps the only statistics reported are the yield of the function and the mean and standard deviation of dice for the function.

As a final remark, recall that the input data implies site yields. Thus, the map interpretation depends on the interpretation given to the site. For instance, if the site yield represents a defect of a specific size x , then the wafer simulated will show the regional distribution of defects. Of course, the radial distributions represent the radial yield of defects at radius R , and, the smaller the die size the more accurate the simulation is, since in this case it represents the position of a defect in the wafer.

7. SUMMARY AND CONCLUSIONS.

Standard tools of statistical means of control have been available for many years. However, their use on a routine basis has been somewhat limited. This is due mainly to a lack of easy access to the appropriate data, the tedious hand plotting of charts or wafer maps and the difficulty of keeping an up to date on line system. Hence, it is essential that this capabilities be accessible in an easy form [18].

ALWAYS provides interactive graphics displays, online screen reports, hardcopy plots, and facilities to store in the database the analysis or simulation just performed, as well as to retrieve previous ones. These analyses can be overlapped over the current composite wafer to do comparisons or simply be placed instead of the current map.

As a part of the user friendly interface a set of color graphics to report wafer maps and distribution charts was included, see Fig. 8. Also any distributions for the simulations can be drawn online. This feature eases the continuous execution of quick simulations for new user's data.

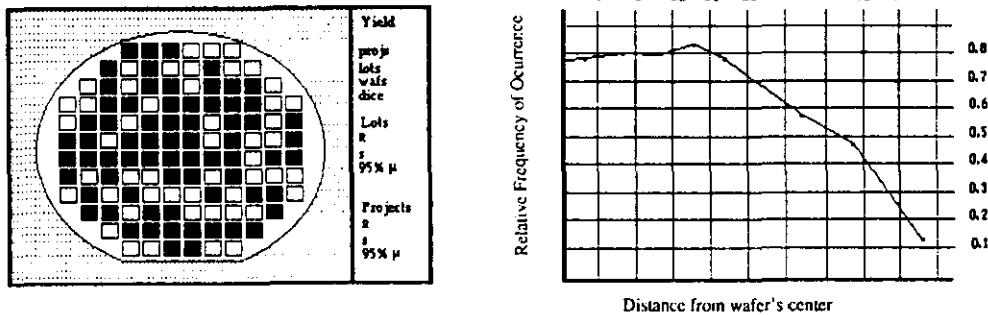


Figure 8. (a)Example of wafer maps. (b)Example of distributions.

To facilitate access to the results of every map analysis, the statistics are reported immediately to their right. They include the yield of the composite wafer, the number of projects, lots, wafers, and dice involved in the analysis, and the yield variation between lots and between projects.

ALWAYS is a program written in C and implemented on an Apollo Domain 3000 Workstation System running Unix BSD4.2. The current version supports static menu screens but later versions will provide pop-up menus. It is not a disadvantage to have static screen menus when the number of nested menus is small, although, the ever increasing availability of UIMSs [21] promotes an upward to this kind of interfaces. Future work involves providing facilities to have dice of different sizes in the same wafer and also facilities to correlate wafers with dice of different sizes and shapes, among others.

We presented a simple, yet complete, package for wafer yield analysis. As in every beginning, things are not that easy. When there were no layout editors, people used to do their designs by hand, or by creating isolated programs to ease this enormous task, suddenly the first layout editors appeared and became more and more popular up to the point where nowadays it is an indispensable and easy to obtain tool. Similarly, the idea of the Wafer Yield Editor shows that it is easy to construct a system to help in the analysis of yield improvement. Sophisticated CAM tools [20] that provide statistical process and quality control, and, analysis and simulation of yield management are also available. However these systems are oriented to automate the wafer processing in silicon foundries and their scope differs from yield analysis. ALWAYS is an example of a tool for research of yield analysis which everybody can make at little expense. ALWAYS is not only suited for usage in the silicon foundry but also in the layout designers rooms, the theoretical yield modelers office, etc.

The most significant features of ALWAYS are summarised as follows:

- 1) A simple database structure allows to examine lots, and individual wafers.
- 2) Full flexibility to edit the characteristics of the prototype wafer.
- 3) The analysis technique allows to estimate the contributions of both correlated and uncorrelated detractors to the total yield. Such information can be used to study the effect of process changes on product yield.
- 4) Simple simulation tools to estimate the wafer yield.

It is our believe that a simple package like ALWAYS provides a positive impact on yield improvement.

REFERENCES

- [1] Ham, W.E.
Yield-area analysis. Part 1: A diagnostic tool for fundamental integrated-circuit process problems.
RCA Rev., Vol. 39(1978), p. 231-249.
- [2] Warner, Jr., R.M.
Applying a composite model to the IC yield problem.
IEEE J. Solid-State Circuits, Vol. SC-9(1974), p. 86-95.
- [3] Stapper, Jr., C.H.
On a composite model to the IC yield problem.
IEEE J. Solid-State Circuits, Vol. SC-10(1975), p. 537-539.
- [4] Ferris-Prabhu, A.V. and L.D. Smith, H.A. Bonges, J.K. Paulsen
Radial yield variations in semiconductor wafers.
IEEE Circuits & Devices Mag., Vol. 3, No. 2(March 1987), p. 42-47.
- [5] Stapper, C.H.
On yield, fault distributions, and clustering of particles.
IBM J. Res. & Dev., Vol. 30(1986), p. 326-338.
- [6] Stapper, C.H.
Yield model for fault clusters within integrated circuits.
IBM J. Res. & Dev., Vol. 28(1984), p. 636-640.
- [7] Gupta, A. and W.A. Porter, J.W. Lathrop
Defect analysis and yield degradation of integrated circuits.
IEEE J. Solid-State Circuits, Vol. SC-9(1974), p. 96-103.
- [8] Yanagawa, T.
Yield degradation of integrated circuits due to spot defects.
IEEE Trans. Electron Devices, Vol. ED-19(1972), p. 190-197.
- [9] Stapper, C.H.
Defect density distribution for LSI yield calculations.
IEEE Trans. Electron Devices, Vol. ED-20(1973), p. 655-657.
- [10] Stapper, C.H.
LSI yield modeling and process monitoring.
IBM J. Res. & Dev., Vol. 20(1976), p. 228-234.
- [11] Stapper, C.H.
The effects of wafer to wafer defect density variations on integrated circuit defect and fault distributions.
IBM J. Res. & Dev., Vol. 29(1985), p. 87-97.
- [12] Stapper, C.H. and F. Armstrong, K. Saji
Integrated circuit yield statistics.
Proc. IEEE, Vol. 71(1983), p. 453-470.
- [13] Walker, H. and S.W. Director
VLASIC: A catastrophic fault yield simulator for integrated circuits.
IEEE Trans. Comput.-Aided Des. Integrated Circuits & Syst., Vol. CAD-5(1986), p. 541-556.

- [14] Walker, D.M.H.
Yield simulation for integrated circuits.
Ph.D. Thesis. Pittsburgh, Pa.: Carnegie-Mellon University, 1986.
- [15] Gupta, A. and J.W. Lathrop
Yield analysis of large integrated-circuit chips.
IEEE J. Solid-State Circuits, Vol. SC-7(1972), p. 389-395.
- [16] Calhoun, D.F. and L.P. McNamee
A means of reducing custom LSI interconnection requirements.
IEEE J. Solid-State Circuits, Vol. SC-7(1972), p. 395-404.
- [17] Maly, W. and F.J. Ferguson, J.P. Shen
Systematic characterization of physical defects for fault analysis of MOS IC cells.
In: Proc. 15th Int. Test Conf., Philadelphia, 16-18 Oct. 1984.
New York: IEEE, 1984. P. 390-399.
- [18] Campbell, D.M. and Z. Ardehali
Process control for semiconducting manufacturing.
Semicond. Int., Vol. 7, No. 6(June 1984), p. 127-131.
- [19] Mallory, C.L. and D.S. Perloff, T.F. Hasan, R.M. Stanley
Special yield analysis in integrated circuit manufacturing.
Solid State Technol., Vol. 26, No. 11(Nov. 1983), p. 121-127.
- [20] Burggraaf, P.
CAM software. Part 1: Choices and capabilities.
Semicond. Int., Vol. 10, No. 6(June 1987), p. 56-61.
- [21] Myers, B.A.
Creating interaction techniques by demonstration.
IEEE Comput. Graphics & Appl., Vol. 7, No. 9(Sept. 1987),
p. 51-60.
- [22] Maly, W. and M.E. Thomas, J.D. Chinn, D.M. Campbell
Double-bridge test structure for the evaluation of type,
size and density of spot defects.
Pittsburgh, Pa.: SRC-CMU Center for Computer-Aided Design,
Department of Electrical and Computer Engineering, Carnegie-
Mellon University, 1987.
Research Report No. CMUCAD-87-2.
- [23] Chen, I. and A.J. Strojwas
A methodology for optimal test structure design for statistical
process characterization and diagnosis.
IEEE Trans. Comput.-Aided Des. Integrated Circuits & Syst.,
Vol. CAD-6(1987), p. 592-600.
- [24] Chen, I. and A.J. Strojwas
Realistic yield simulation for IC structural failures.
In: Digest of Tech. Papers 4th IEEE Int. Conf. on Computer-
Aided Design (ICCAD-86), Santa Clara, Cal., 11-13 Nov. 1986.
New York: IEEE, 1986. P. 220-223.

- [25] Freund, J.E. and R.E. Walpole
Mathematical statistics. 3rd ed.
Englewood Cliffs, N.J.: Prentice-Hall, 1980.
Prentice-Hall mathematics series

- [26] Chen, I. and A.J. Strojwas
Realistic yield simulation for VLSIC structural failures.
IEEE Trans. Comput.-Aided Des. Integrated Circuits & Syst.,
Vol. CAD-6(1987), p. 965-980.

- [27] Fantini, F. and C. Morandi
Failure modes and mechanisms for VLSI ICs: A review.
IEE Proc. G, Vol. 132(1985), p. 74-81.

- [28] Edwards, D.G.
Testing for MOS IC failure modes.
IEEE Trans. Reliab., Vol. R-31(1982), p. 9-18.

- [29] Taylor, R.G. and E. Stephens
Microcircuit failure analysis.
Br. Telecommun. Eng., Vol. 4(1985), p. 39-46.

ALWAYS
User's Manual

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1. A TUTORIAL.

This section is not intended to give an exhaustive explanation of ALWAYS, it is rather aimed to demonstrate the essential features of ALWAYS in a normal session, but without getting down into formal rules. For more details refer to the report or to the user's manual. This tutorial assumes that the user is seated behind a terminal with ALWAYS running. The tutorial example is located in the directory PATH/always.tutorial.

The wafers to be analysed consist of a sequence of tests to evaluate the threshold voltage adjustment at EFFIC* . Four lots are derived, two are for depletion transistors and the others for enhancement transistors. Thus we created two projects, one is called "depletion" and the other "enhan".

EFFIC uses wafers of 3 inches of diameter, and the size of the dice in question is 5.8mm by side. The results of the measurements are stored in a directory named PATH/measurements. We created a filter to interpret these results for ALWAYS, first we evaluate the average and standard deviations of the threshold voltages in each wafer, then knowing these values we make a process window of acceptance of the voltage value. We say that the threshold voltage is good if its value lays within -3σ and $+3\sigma$ of the average value. Next, we simply pass from the coordinate system of the ATE to ours for more convenience and simplicity. Finally we repeat these steps for each one of the wafers.

As a word of comment, all the wafers were not processed identically, some variations, as the concentration of dopants, were changed. Hence, in the following discussion we avoid making any statistical inferences of the results. We simply use them to show some of the features of ALWAYS. The "real life" configuration of the dice in the wafers to be analysed is shown in Fig. 1.

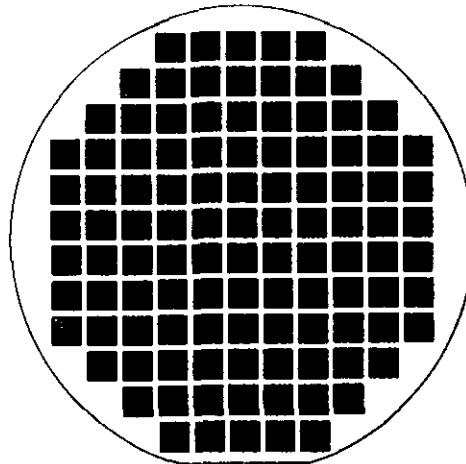


Figure 1. Dice configuration in the EFFIC wafers.

* Eindhovense Fabricage Faciliteit voor geIntegreerde Circuits.
(Eindhoven Fabrication Facility for Integrated Circuits.)

1.1 GETTING STARTED.

Start ALWAYS by typing

always <CR>

As we already mentioned, ALWAYS stands for "AnaLyser of Wafer YieldS", the current version is 1.0, we hope to make more improvements. Now try clicking the left button of the mouse. This button is used to point at any of the menu selections, the button in the center is used to show analyses previously stored and the button to the right is used to exit the program, this can be done by doubleclicking it.

You are now facing the main menu options of ALWAYS. At the top are displayed the characteristics of the prototype wafer, and as we can see they differ very much from our "real life" wafer.

Move the cursor to the *edit* option and click the left button. This menu allows to edit the characteristics of the prototype wafer. First we know that our dice are bigger, thus click in the *die size* option, you will be asked to enter the horizontal and vertical dimensions of the new die. Now change the size of the wafer to 76mm by clicking in the *wafer size* option and entering this new value.

So far we already have the correct wafer and dice dimensions but the configuration is still different. The filter program that we mentioned, assumes that the rightmost die and closest to the flat side of the wafer has coordinates (8,0). We can investigate which are the coordinates of this die, or any other, by clicking in the *X/Y* option and then clicking in the die itself. The mask size is 73mm, thus, we need to displace the wafer 1.6mm to the right and 1.6mm down from the center of the mask.

Adjust first the mask size by clicking in the *mask size* option and enter the new dimension, and later switch to the adjustment menu by clicking in the *adjustment* option. Set here the step size to 0.4mm and then move the wafer four times to the right and four times down. Of course you are free to give any other step size of your choice.

Now we are able to proceed with the analysis. The red bar down to left of the screen is the "done/exit" bar. Clicking once in this bar we will return to the edit menu, and clicking again it will position us back in the main menu.

Let us select now the data for the analysis. Click in the *set* option. We are facing now the "set" menu which allows us to set projects, lots and wafers for our analysis.

Let us pick up first the enhancement data. Click in the *project* option. To the right of the screen are displayed all the projects that are present in the current directory. In our case there are only two. The "depletion" and the "enhan" projects. Since we said that we are going to analyse first the enhancement data click in the *select* option and then in the "enhan" project. The name of the project should have been highlighted, otherwise try again. Now click in the "done/exit" bar to indicate that we want that project; this last action is interpreted as "done" with the menu and "exit" it, so we are positioned again in the "set" menu. Now let us choose the lots.

Click in the *lots* option. In a similar fashion to the projects, the lots are displayed to the right of the screen. These lots are the lots that belong to the project previously chosen, that is, project "enhan". Select the lot 5600. We have now the project and the lot for our analysis. Try to select wafer 5600e1 by doing similar operations to the project or lot selection.

Click in the "done/exit" bar until we get back to the main menu again. Now you will see in the three small windows to the right the project, lots, and wafers involved for the analysis.

We have now the correct prototype wafer and we already chose the data for the analysis, so let us analyse this data. Click in the *analysis* option, at the bottom you will see displayed a message informing that ALWAYS is loading the data corresponding to the wafer 5600e1. After the loading is completed we can face then the "analysis" menu. Remember that we selected only one wafer, thus some options will be meaningless, although you are free to try them.

We will find first all the good dice in the wafer, so, click in the *functional map* option. The dice displayed in green are the good dice, the rest are blank. To the right are some statistics. Mainly they are the yield of good dice, the number of projects, lots and wafers involved in the analysis, the average lot yield, the variations in the lot yield, the project average and variation yield and finally the expected number of dice that accomplish the function. Since we have only one wafer, one project, and one lot, the project and lot variation values are the same.

Now find the bad dice, thus click in the *zero map*. The dice in red are the bad dice. To the right are also displayed statistics corresponding to this map. The yield shown is now for bad dice.

Click now in the *distribution* option to check the radial and angular distributions of this wafer. Click first in the *radial* option, you will be asked to give the site yield, type 100 to mean that we want to find the radial distribution of good dice.

Now let us see the angular distribution, click in the *angular distribution* option and answer also with 100 for the site yield.

If you try a number other than 100 or 0, ALWAYS will try to adjust it with respect to the number of existing wafers in the analysis, for instance if you type 75% there is obviously no 75% yield, there is only 0 or 100% since we have only one wafer. Thus, ALWAYS will respond with the analysis for 0%. Remember that our interpretation of site yield implies the number of projected dice, from all the wafers, that accomplish a function.

At this point we assume that you are already more or less familiar with the selection of data, so let us add more data to the analysis. Click twice in the "done/exit" bar to go back to the main menu. Now go to the "set" menu and select all the wafers of the lot 5600. So, click in the *wafers* option then click in *select* option and then click through each one of the wafers, after you have selected all the wafers click in the "done/exit" bar to indicated that we want all those wafers (done) and that we want to go back (exit). Now select also all the wafers of lot 5500. Click in the *lots* option and then in the *select* option, then click twice in the 5500. This last action will select all the wafers of lot 5500 because ALWAYS allocates, when two projects or two lots are selected immediately one after each other, all the elements of the second to last selected item.

Now go again to the "analysis" menu, so click in the "done/exit" bar and then in the *analysis* option. Let us investigate one of the variable maps, click in the up-range map and answer with 50, this means that we want to see the dice that were good through half or more of the wafers in the analysis.

Now click in the "distributions" option and then click in the "frequency" option, this last option will display a histogram of the frequency of occurrence of each site yield.

Before we continue it would be good that you investigate the several options for the analysis by yourself. Take your time ...

We shall see now the different tools that we have in ALWAYS, so place yourself in the main menu and click in the *tools* option. Click now in the *retrieve* option, this option will display, and allow you to select, analyses previously stored in the database, you will see only one called "5601e", which is the one that we created for the purposes of this tutorial. Click in the name of the analysis to retrieve it. On screen you will see the characteristics of the analysis. It is a

functional map of one of the wafers. Now click in the *overlap* option. This action enables, as its name says, the "overlap" function. That is, whenever we are dealing with any analysis and we want to do an overlap of wafers between the retrieved from the database and the one created from the analysis we use this function, and if we want to swap wafers we use the "alternate" option. Now, click in the "done/exit" bar to go back to the main menu and then click in the *analysis* option.

Choose now the info-map, so click in there, and after the analysis is finished click the middle button of the mouse. This action will overlap the wafer that we have just retrieved over the info analysis. The combination of an individual wafer and the info-map of all the wafers allows to see the contribution to yield improvement or detracton of the single wafer.

The overlap and alternate functions act as toggles, so to get the initial info-map click again the middle button of the mouse and see how does the retrieved map disappear.

The last feature that we are going to review is the wafer map simulation. Go to the main menu and click in the *simulate* option and then click in the *wafer map* option. In order to simulate wafer maps we must provide the number of wafers to be simulated, the upper radial yield and finally the lower radial yield. If any of this conditions is missing the simulation will not run.

Now, let us say that we want to simulate a lot of 10 wafers. Click in the *# wafers* option and then type 10 in the field to the right of the screen. Click in the *upper distribution* in order to set the upper radial yield. A new menu will appear, click in the *retrieve* option. This option retrieves all the distributions existing in the database. In this case there is only one, the "upper". Click on its name and wait until it is drawn on screen, at that moment ALWAYS knows already which is the upper yield distribution. We are missing only the lower yield. Click in the "done/exit" bar to go backwards and then click in the *lower distribution* option.

ALWAYS provides several mechanisms to capture a distribution, we already tried one, the retrieval, another one is to create the ditribution file in advance by typing it, and the last alternative is to draw it directly on screen. We shall try this last option.

Click in the *draw* option. ALWAYS paints a grid whose ordinate is the wafer radius, and the absice is the radial yield. Try to draw the distribution shown in Fig. 2. First click in the grid at coordinates (0,0.6), they are also displayed at the right side of the screen, this is the initial point, a rubberband for line drawing will appear, direct the rubberband to the next point and click there, the rubberband should have been fixed up to the new point and a new rubberband starting at the last point appears. Continue to do so until you finish drawing the distribution. If you commit a mistake click the middle button of the mouse to undo the last line. To finish drawing click in the "done/exit" bar.

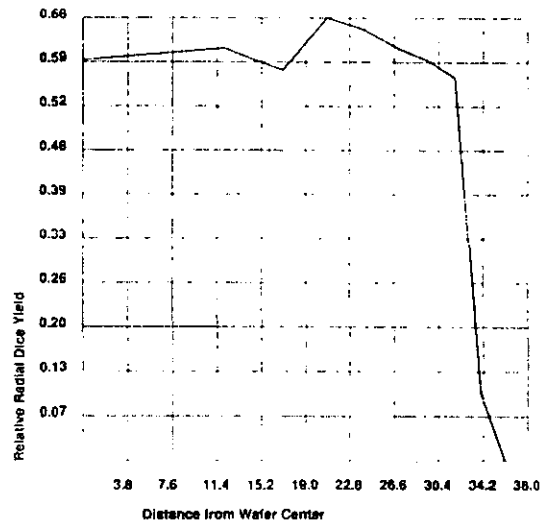


Figure 2. Lower relative radial yield for the example.

Now let us run the simulation, so click in the *run* option. The simulation phase starts automatically and every wafer is displayed. After the simulation is finished the wafers can be viewed through the *view* option and also they can be analysed through the *show map* option. These analyses are the same that we investigated before.

From now on you are on your own, have an enjoyable time with ALWAYS, and good luck !!!

2 USERS MANUAL

ALWAYS is a system used for spatial yield estimation and prediction of wafers. It is able to quantify yield variations between *lots* of wafers and between the wafers themselves by doing wafer map and distribution analyses. Its features are explained in detail through the rest of this manual.

2.1 USER INTERFACE.

ALWAYS assumes that the current directory contains all the projects to be analysed. The taxonomy of ALWAYS is shown in Fig. 3. In it are shown in detail the options of the system and the nesting levels of the menus.

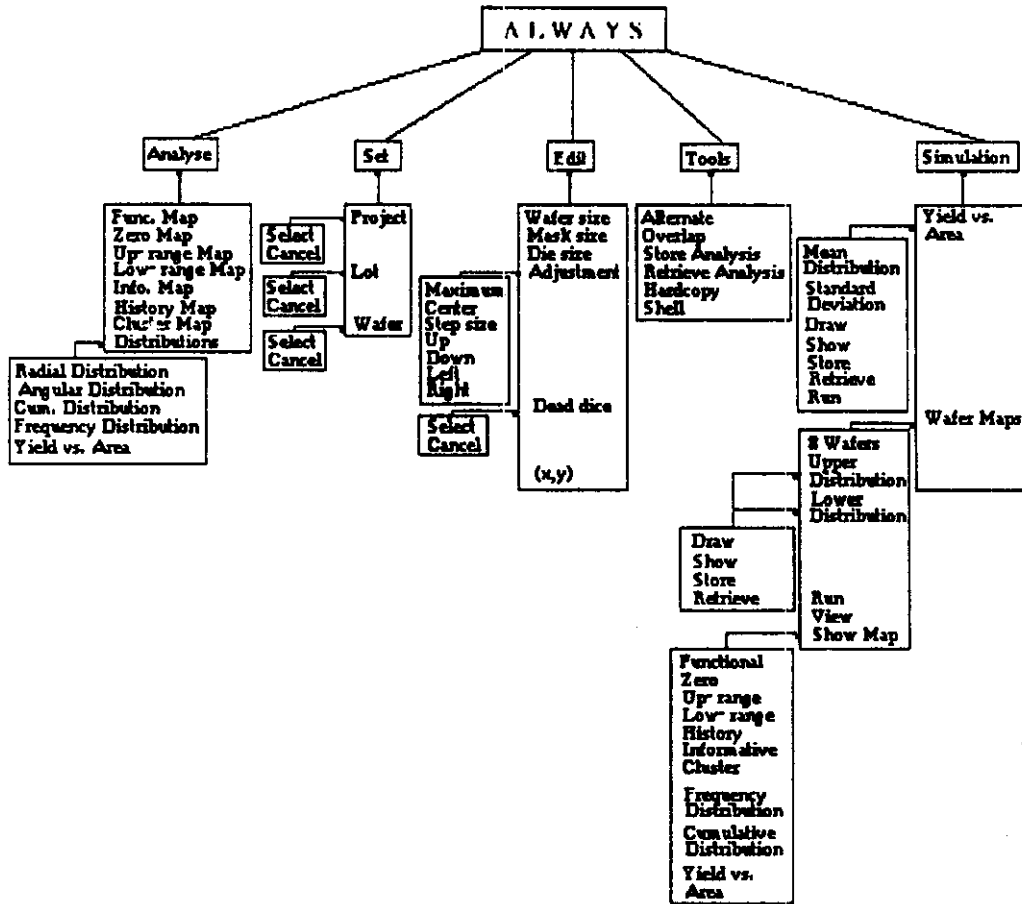


Figure 3. Taxonomy of ALWAYS.

The following are the interfaces required to work with ALWAYS.

- **MOUSE INTERFACE.** ALWAYS is a highly interactive system that makes use of mouse based interface systems. The left button of the mouse is used to point at any of the options of the menus. The button in the middle is in effect when the "overlap" or "alternate" options are enabled or at the moment of capturing information in the "simulation" menu. The button to the right is used to exit ALWAYS at any moment by doubleclicking it.
- **DONE/EXIT BAR.** In the lower left corner of the screen a red bar called the "done/exit" bar is constantly displayed. This bar has two effects, one is to confirm any operation realised in

the menu, such as to capture data curves in the simulation menu, and its other use is to go one menu backwards. For instance, if it is desired to go back from the "adjust" menu to the main menu, then by clicking once on the bar, ALWAYS positions itself in the "edit" menu, and then by clicking on the bar again, the main menu is achieved.

- **INPUT FORMAT.** The input data of ALWAYS consists of the status, good or bad, of each die in every wafer for all the lots and projects to be analysed. The "project" and the "lot" are directories and the "wafer" is the file characterising the information. The project directory has to be as follows :

project_name .pro
the lot directory like
lot_name .lot
and the wafer file as
wafer_name .waf

The data in the wafer file is given as coordinates with the status of the die, the format is as follows:

(x , y) = 1
for good dice, or
(x , y) = 0
for bad dice, x and y represent the coordinates of a die inside the wafer.

- **ERROR REPORT.** If there were errors in the wafer files, ALWAYS generates a file containing information of these errors, i.e that a die is out of the wafer, or out of the mask, etc. The name of this file is
"always.errors".

Mistakes comitted during the session are reported in the interface line, this kind of errors are for instance an invalid die size, or trying to select a lot without having selected a project first, etc.

- **INVOCATION.** ALWAYS has also a configure file that presets the size of the wafer, of the mask and of the dice. The name of this file is
"config.always"

and its syntax is as follows :

w N
m N
x N
y N
h N
v N

where N represents the size in all the cases, and

w - wafer size
m - mask size
x - die size in x direction
y - die size in y direction
h - wafer shiftment with respect to the mask in x direction
v - wafer shiftment with respect to the mask in y direction

These options can also be given interactively at the moment of starting ALWAYS as:

always -wN -mN -xN -yN -hN -vN -i

The -i option is to tell ALWAYS to ignore the configure file, if it exists.

- **DATABASE FILES.** Every analysis stored by ALWAYS with the "store" option in the tools menu is characterised by

analysis_name .ana
and in the simulation section by

distribution_name .dst

The analysis file is a non ASCII file and thus is not readable. The format of the distribution file is

x f(x)

where

x - domain of the function

f(x) - the function

Both files are stored in the current directory.

2.2 MAIN OPTIONS.

This is the main menu of the system. From here it is possible to edit a wafer, to select the data for the analysis, to carry on an analysis, to make simulations, and to use the miscellaneous tools. The main menu screen is shown in Fig. 4.

At the top are displayed the characteristics of the prototype wafer. These characteristics are the size of the wafer, the size of the mask, and the size of the dice. At the right are three small windows named PROJECT, LOT, and WAFER respectively. These windows contain the information of the data involved for the analysis. If the name of a project is clicked, all its lots and all its wafers are highlighted, furthermore, if one clicks at one of the lots of the project all the wafers that belong to that specific lot will be highlighted. It is possible to scroll in each of the windows by clicking in the arrows.

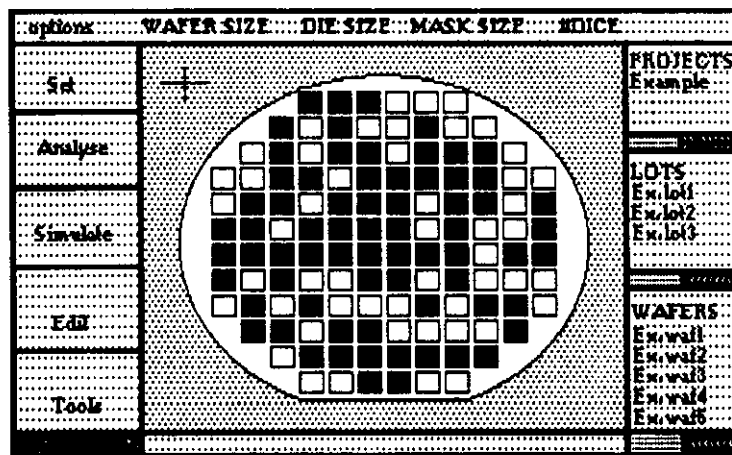


Figure 4. Main menu.

- SET. This option allows to select, or to cancel, projects, lots and wafers for the analysis.
- ANALYSE. This option allows to carry on several types of analyses on the wafers selected for this purpose.
- SIMULATE. This option allows to simulate the yield vs. area or to simulate wafers maps based upon the characteristics of the prototype wafer.
- EDIT. This option allows to edit the characteristics of the prototype wafer
- TOOLS. This option is used to save or retrieve data in the database, and to use other tools.

2.3 WAFER EDITING.

This menu allows to change the characteristics of the prototype wafer. The changes are the size of the wafer, the size of the mask, the size of the dice and the displacement of the wafer with respect to the mask. It is also possible to select here the dead dice, and to visualise the coordinates of each of the dice in the wafer. The edit menu is shown in Fig. 5. When ALWAYS asks to enter any numerical information the only keys which are enabled are: 1, 2, 3, 4, 5, 6, 7, 8, 9, 0, ., BACKSPACE, CR. ALWAYS interprets the data when the <CR> key is pressed; if an undesired number is keyed, it can be erased with the <BACKSPACE> key.

wafer size		
mask size		
die size		
adjust		
dead dice		
x / y		

Figure 5. Edit Menu

- **WAFER SIZE.** By clicking in this option ALWAYS asks to enter the new size of the wafer. This inquiry is present in the form of a field at the right side of the screen.
- **MASK SIZE.** This option allows to modify the size of the mask. The new size is also entered in a field at the right side of the screen.
- **ADJUST.** This option allows to displace the wafer from the center of the mask. For more details refer to the wafer displacement section.
- **DEAD DICE.** This option allows to select the dead dice. The dead dice are dice that are not considered for the analysis. In this form one can selectively activate or deactivate regions in the wafer. When one clicks in this option a new "select/cancel" menu appears. If the select option is clicked then ALWAYS is ready to create dead dice in the wafer. To create any dead die just click in its position in the wafer. To cancel dead dice first click in the cancel option and then in any of the existing dead dice. The current dead dice are lost if there is a modification made to the wafer size, mask size, or die size.
- **X / Y.** This option allows to visualise the numerical coordinates of a die. To see the coordinates of a die, click in its position in the wafer. The numerical coordinates appear to the right of the screen and the die selected is highlighted.

2.3.1 WAFER DISPLACEMENT.

This menu offers the ability to displace the wafer from the center of the mask, to recenter the wafer and the mask, and to find the maximum number of dice that can be accommodated in the wafer. The adjust menu is shown in Fig. 6.

maximum		
center		
step size		
up		
down		
right		
left		

Figure 6. Wafer Displacement Menu

- **MAXIMUM.** This option configures the dice in the wafer in such a form that the wafer contains the maximum possible number of dice.
- **CENTER.** This options aligns the center of the wafer with the center of the mask.
- **STEP.** This is the incremental step used to displace the wafer from the mask. Its value is displayed immediately below the title.
- **UP.** This options moves up the wafer from the mask.
- **DOWN.** This option moves down the wafer from the mask.
- **LEFT.** This option moves the wafer to the left of the mask.
- **RIGHT.** This option moves the wafer to the right of the mask.

2.4 INPUT DATA SELECTION

This menu allows to select the projects, lots, and wafers that will be used for analysis. The selection of data is hierarchical. In order to select any wafer, its lot and its project should have been selected previously. This menu is shown in Fig. 7.

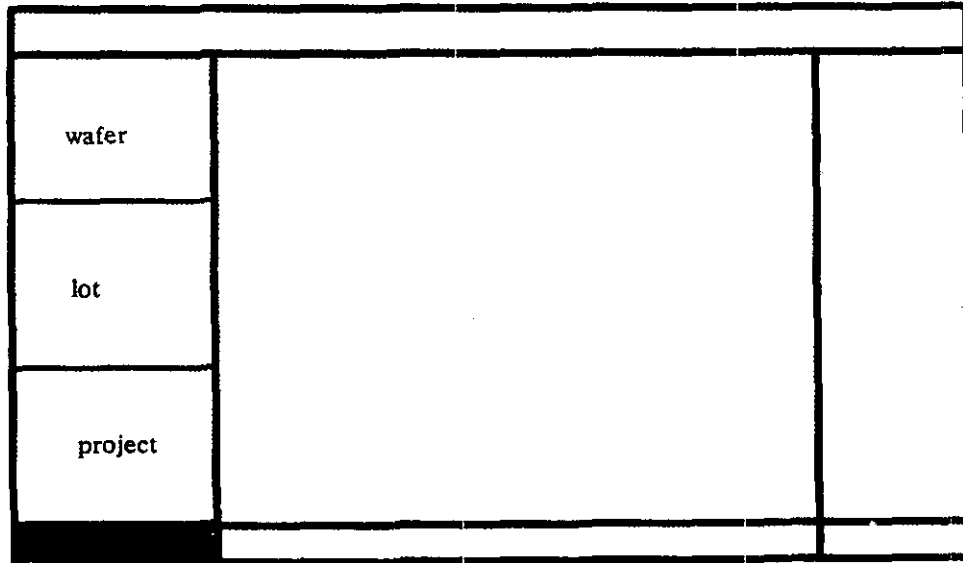


Figure 7. Data selection Menu.

- **WAFER.** This option selects individual wafers from the lot and project currently active. A second menu with the options of "select" and "cancel" appears. By clicking the "select" option the names of the existent wafers appear to the right of the screen, in order to make them active, click on their names. The name just picked up is highlighted in red. To deactivate wafers, click in the "cancel" option and then click in each of the activated wafers. The arrows in the lower right corner are used to scroll through wafers if their number exceeds the size of the window.
- **LOT.** This option selects the lots of the project currently active. A second menu with the options of "select" and "cancel" appears. To activate any lots click in the "select" option. To deactivate any lots click in the "cancel" option. If during the activation process the name of a lot is clicked twice, or two lots are selected consecutively, for the first time, then the second to last lot will be made active and also all the wafers belonging to it are made active as well. The existent lots are displayed to the right of the screen. Each lot that is "selected" or "canceled" is highlighted in red. The arrows in the lower right corner are used to scroll through lots if their number exceeds the size of the window.
- **PROJECT.** This option selects the projects available in the current directory. A second menu with the options of "select" and "cancel" appears. To activate any projects click in the "select" option. To deactivate any projects click in the "cancel" option. If during the activation process the name of a project is clicked twice, or two projects are selected consecutively, for the first time, then the second to last project will become active and also all the lots and all the wafers belonging to each lot are made active as well. The existent projects are displayed to the right of the screen. Each project that is "selected" or "canceled" is highlighted in red. The arrows in the lower right corner are used to scroll through projects if their number exceeds the size of the window.

2.5 YIELD ANALYSIS.

This option offers the ability to carry on several wafer map and distribution analyses. All the analyses make use of the wafers selected in the SET option. All the user's yield value inputs are assumed to be in per centage.

2.5.1 WAFER MAP ANALYSIS.

The menu option for wafer map analysis is shown in Fig. 8. Each analysis is accompanied of a set of statistics that reflect the variations between wafers, lots, and projects. For more details on the analysis options and on the statistics refer to the system description in the first section of this EUT report.

functional map		
zero map		
up-range map		
low-range map		
history map		
info map		
cluster map		
distributions		

Figure 8. Analysis Menu

- **FUNCTIONAL MAP.** This map shows all the dice that were good all the time in the whole set of wafers involved in the analysis. The dice that are good are displayed in green.
- **ZERO MAP.** This map shows all the dice that were bad all the time in the whole set of wafers involved in the analysis. The dice that are bad are displayed in red.
- **UP-RANGE MAP.** With this option it is necessary to specify the minimum site yield to be displayed. This is done by entering the yield value in the field to the right of the screen. The map will display all the dice that have a site yield equal or bigger than the one specified. The dice that have a bigger site yield are displayed in yellow and the ones that have the specified site yield in magenta. ALWAYS rounds the specified yield to the lower nearest yield since the site yield depends on the number of wafers available for the analysis. Consider the case where there is only one wafer active and an up-range of 67% was specified. Obviously for this case there are only two site yields, 0 and 100. For this example ALWAYS will round the site yield to 0% and will display the bad dice in magenta and the good dice in yellow.
- **LOW-RANGE MAP.** With this option it is necessary to specify the maximum site yield to be displayed. This is done by entering the yield value in the field to the right of the screen. The map will display all the dice that have a site yield equal or lower than the one specified. The dice that have a lower site yield are displayed in yellow and the ones with the specified yield in magenta. ALWAYS rounds the specified yield to the lower nearest yield since the site

yield depends on the number of wafers available for the analysis. Consider the case where there is only one wafer active and a low-range of 67% was specified. Obviously for this case there are only two site yields, 0 and 100. For this example ALWAYS will round the site yield to 0% and only the bad dice are shown.

- **HISTORY MAP.** This map displays the site frequency of each die numerically.
- **INFO MAP.** This is mainly a contour map. It shows the dice that have the average site yield of the analysis, and those dice that have a site yield above or below the average. The dice that have the average site frequency are displayed in blue, the dice that have a site frequency above the average are displayed in magenta, the dice that have a site frequency below the average in cyan, and finally the dice with zero site yield in red.
- **CLUSTER MAP.** This option finds clusters in the composite wafer. The specific site yield and the minimum number of elements to make a cluster are asked as data. The map will display all the dice which accomplished these conditions. The clustered dice are shown in purple. The statistics show the number of groups of clusters and the number of clustered elements.
- **DISTRIBUTIONS.** These option is to carry on distribution analyses.

2.5.2 DISTRIBUTION ANALYSIS.

The distribution menu is shown in Fig. 9.

radial distribution		
angular distribution		
cumulative distribution		
frequency distribution		
yield / area		

Figure 9. Distribution Menu

- **RADIAL DISTRIBUTION.** This options asks for the site yield which is going to be looked for radially. This data is entered in the field to the right of the screen. The graph shows the radial yield of dice that have a site yield equal or above the user's yield. If zero is specified, then the graph shows the absolute radial yield of the composite wafer. If <CR> is typed alone it is interpreted as zero.
- **ANGULAR DISTRIBUTION.** This option also asks for the site yield which is going to be looked for angularly. This data is entered in the field to the right of the screen. The graph shows the angular yield of dice that have a site yield equal or above the user's yield. If zero is

specified, then the graph shows the absolute angular yield of the composite wafer. If <CR> is typed alone it is interpreted as zero.

- **CUMULATIVE DISTRIBUTION.** This option shows the cumulative distribution of site frequencies.
- **FREQUENCY DISTRIBUTION.** This option shows the frequency of occurrence of the different site yields for all the dice in the composite wafer. The information is displayed in a histogram fashion.
- **YIELD vs. AREA.** This option evaluates the yield vs. area of the composite wafer. The user is also asked to give the site yield which is going to be searched. The graph displays the yield of the dice that have a site yield equal or bigger than the user's for several area sizes. If zero is specified, then the absolute yield vs. area of the composite wafer is shown, <CR> alone is also interpreted as zero.

2.6 SIMULATIONS.

ALWAYS provides two kinds of simulations, one is a yield vs. area simulation and the other is the creation of wafer maps. When using the "draw" option to capture distributions for simulations, ALWAYS assumes that the last y coordinate remains constant if the distribution was not drawn up to the maximum value of the domain of the function. For instance, if the maximum value of the domain is, let us say 35, and the last coordinates drawn were (23, 0.8), ALWAYS assumes that from the domain 23 to 35 the function has a constant value of 0.8.

2.6.1 YIELD vs. AREA SIMULATION.

This simulation is based on the negative binomial formula of yield. ALWAYS offers several alternatives to feed the input data to the yield formula. It is possible to give the mean and standard deviations of the distribution, or to draw on line the distribution and to store it for future use, or to retrieve any distributions existing in the database. The mean and standard deviations of any distribution are shown in the fields in the mean distribution and standard deviation options. The distribution represents the number of defects per die. The menu is shown in Fig. 10.

mean distribution		
standard deviation		
draw		
show		
store		
retrieve		
run		

Figure 10. Yield/Area Simulation Menu

- **MEAN DISTRIBUTION.** This is the mean of the population of the hypothetical sample. The value is entered in a field to the right of the screen.
- **STANDARD DEVIATION.** This is the standard deviation of the population of the hypothetical sample. The value is entered in the field to the right of the screen.
- **DRAW.** If this option is chosen, ALWAYS is able to interpret the distribution drawn on screen. First it is necessary to specify the maximum value for the domain of the function in the field to the right of the screen and then the maximum value of the function in the same field. Next, ALWAYS draws a grid with the dimensions specified by the user. To draw something point at a location in the grid and then click the first button, a rubberband line should appear, by clicking the first button again the line is fixed and the coordinates, shown at the right side, are saved by ALWAYS, if a mistake is committed, then click the middle button to undo the last line. To stop drawing, select any of the options in the select region, or the "done/exit" bar.

- **SHOW.** This options shows the current distribution used in the simulation.
- **STORE.** This option stores in the database the last distribution drawn. The user is asked to give the name of the file in the interface line. The file will be characterised by ".dst" in the database.
- **RETRIEVE.** This option retrieves all the distributions from the database. They are shown to the right of the screen. To make one active, click on its name and wait until it is displayed on screen.
- **RUN.** This option executes the simulation. The result appears as a graph with the yield versus the number of times of the die area.

2.6.2 WAFER SIMULATIONS.

In this menu it is possible to simulate the individual wafers of a lot. In order to carry on a simulation it is necessary to specify the number of wafers and the relative upper and lower radial distributions of good dice. The menu is shown in Fig. 11.

# wafers		
upper distribution		
lower distribution		
run		
view		
show map		

Figure 11. Wafer Map Simulation Menu

- **# WAFERS.** Enter the number of wafers of the lot in the field to the right of the screen.
- **UPPER DISTRIBUTION.** This option allows to specify the upper radial distribution. For details refer to the section radial distributions.
- **LOWER DISTRIBUTION.** This option allows to specify the lower radial distribution. For details refer to the section radial distributions.
- **RUN.** This option executes the simulation. The simulation process for each wafer is shown on screen. Dice in green are good, and dice in red are bad.
- **VIEW.** This option allows to view the simulated wafers individually. The wafers are displayed to the right of the screen. To make one active, click on its name. The dice shown in green are good, and the dice in red are bad. These wafers are maintained only temporarily, if a new simulation is executed they are lost and the new set of wafers is made active. To store permanently any of the wafers, view it and then go to the tools menu and store it as an

analysis. When ALWAYS is exited, the wafers are deleted.

- **SHOW MAP.** This option allows to carry on several map analyses on the composite simulated wafer. For details refer to the map analyses.

2.6.2.1 RADIAL DISTRIBUTIONS

This menu is the same for the upper and lower distributions. The distribution can either be retrieved from the database or be drawn on screen. The menu is illustrated in Fig. 12.

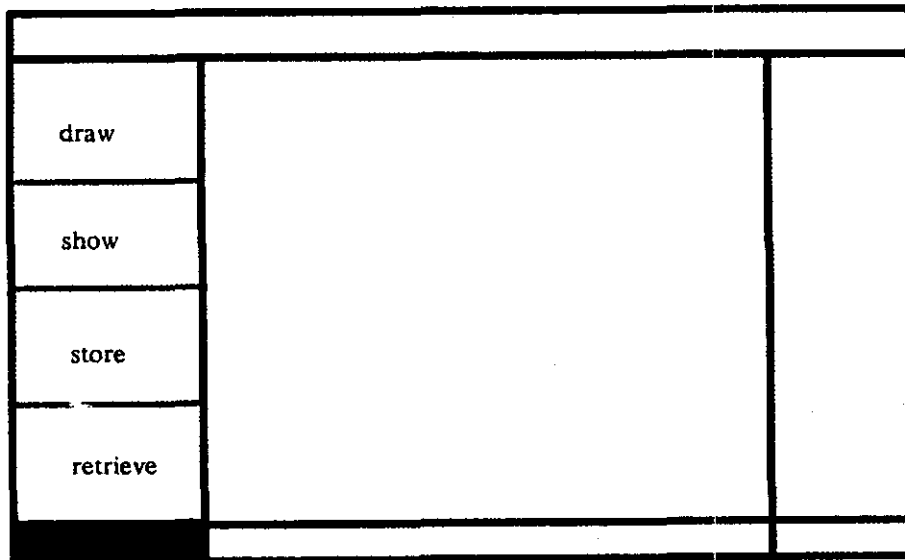


Figure 12. Radial distribution Menu

- **DRAW.** If this option is chosen, ALWAYS is able to interpret the distribution drawn on screen. ALWAYS draws a grid with the ordinate size equal to the radius of the prototype wafer, and the abscissa size equal to one. To draw something point at a location in the grid and then click the first button, a rubberband line should appear, if one clicks the first button again the line is fixed and the coordinates, shown at the right side, are saved by ALWAYS, if one commits a mistake, then click the middle button to undo the last line. To stop drawing, select any of the options in the select region.
- **SHOW.** This options shows the current distribution used in the simulation.
- **STORE.** This option stores in the database the last distribution drawn. The user is asked to give the name of the file in the interface line. The file will be characterised by ".dst" in the database.
- **RETRIEVE.** This option retrieves all the distributions from the database. They are shown to the right of the screen. To make one active, click on its name and wait until it is displayed on screen.

2.7 MISCELLANEOUS TOOLS.

The several tools that ALWAYS offers are to store and retrieve analyses in the database, to allow to overlap and to alternate retrieved wafers with wafers generated during the present analysis, and to make a hardcopy of the analysis or simulations. The "tools" menu is shown in Fig. 13.

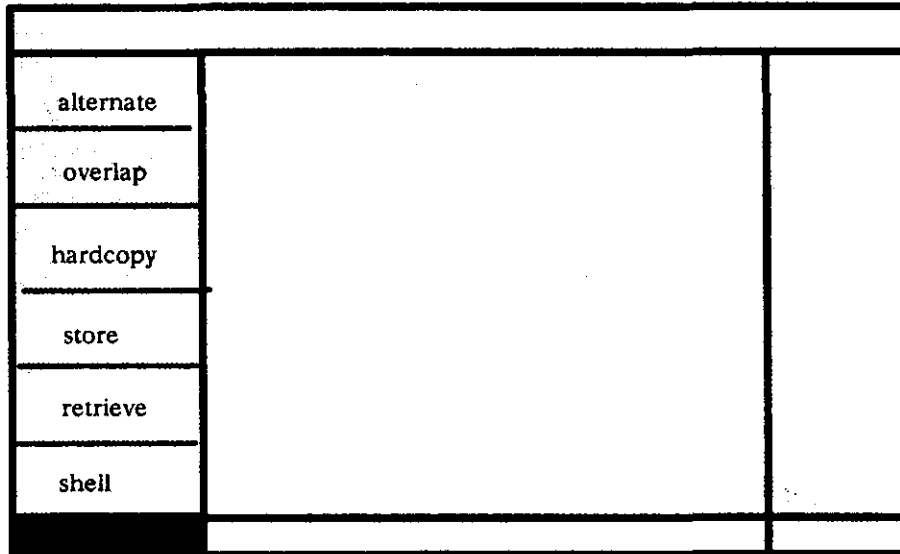


Figure 13. Tools Menu

- **ALTERNATE.** When an analysis is retrieved from the database this option allows to alternate it with any other analysis in the analysis menu. This option is enabled here and it has effect only in the analysis menu. By clicking the middle button in that menu, whatever is displayed is swapped with the currently retrieved analysis. If the middle button is clicked again then the original analysis is restored. Thus, the function acts as a toggle. The dice of the retrieved analysis are shown in orange.
- **OVERLAP.** When an analysis is retrieved from the database this option allows to overlap it over any other analysis in the analysis menu. This option is enabled here and it has effect only in the analysis menu. By clicking the middle button in that menu, whatever is displayed is overlapped by the currently retrieved analysis. If the middle button is clicked again then the original analysis is restored. Thus, the function acts as a toggle. The dice of the retrieved wafer are in orange and any die collapsing with the current analysis is shown in gray.
- **HARDCOPY.** This option creates a plotfile of the last analysis or simulation performed. The plotfile is in postscript format and it is called "always.print". ALWAYS asks for text which is used as a comment to the plot. This text is entered in the interface line. If no text is given the hardcopy is aborted. The file can be spooled for printing.
- **RETRIEVE.** This option allows to retrieve an analysis from the database. A list of analysis is displayed to the right of the screen. An analysis is selected by clicking on its name. Immediately after an analysis has been retrieved its characteristics are displayed on screen, i.e. if it is a functional map, its yield, the size of the wafer used, etc.
- **STORE.** This option allows to store the last analysis performed in the database. The name of the file is asked in the interface line. If no name is given and only <CR> is typed the function is aborted.

- **SHELL.** This option is used to stop ALWAYS temporarily and to go back to the system's shell. To return to ALWAYS type < CTRL-D >.

3 DIAGNOSTICS AND TROUBLESHOOTING

There are basically two types of diagnostics. One is referred to as user diagnostics and it concerns all the interface messages between the user and ALWAYS. The other type of diagnostics are referred to as system diagnostics. These messages deal with the internal programming of ALWAYS such as to allocate memory space for wafer maps, or to search for wafer files, etc. The latter type of diagnostics appear only when there are conflicts between ALWAYS and the operating system.

3.1 USER DIAGNOSTICS

The following are the error messages displayed by ALWAYS. A brief explanation of its meaning is given. These messages appear as a result of an incorrect usage of the features of ALWAYS. Their interpretation during the session is straightforward.

Analysis can be corrupted, check 'always.errors' for errors ...

It was found during the loading of the wafer data that some dice are illegal. Inspect the file always.errors for specific details on these dice.

Invalid wafer size

The size of the wafer is zero.

Invalid mask size

The size of the mask is zero.

Invalid die size

The size of the die is zero.

Impossible to draw wafer, check sizes

This occurs when an attempt to draw the wafer is made but any of the wafer size, the mask size, and the die size is incorrect.

Dead site position out of wafer

If the wafer is displaced from the mask ALWAYS verifies that the dead dice remain within the wafer.

Non existent dead site

An attempt to cancel a non existent dead die was made.

Wafer size is not available

The wafer size was zero at the moment of finding the maximum number of dice in the wafer.

Mask size is not available

The mask size was zero at the moment of finding the maximum number of dice in the wafer.

Die size is not available

The die size was zero at the moment of finding the maximum number of dice in the wafer.

Errors in 'configure' file

Syntax errors were detected in the file "always.config"

Project was not previously allocated

An attempt to cancel a non active project was made.

Lot was not previously allocated

An attempt to cancel a non active lot was made.

Wafer was not previously allocated

An attempt to cancel a non active wafer was made.

Non analysis has been performed

An attempt to store or to hardcopy a non existent analysis was made.

Out of boundary

While drawing a distribution an attempt to draw out of the grid was made.

Function definition violated

More than one value for the same domain value was tried to be drawn.

Non existent simulations

An attempt to retrieve inexistent simulations was made.

Non existent distributions

An attempt to retrieve inexistent distributions was made.

Non existent analysis

An attempt to retrieve inexistent analysis was made.

Non existent projects

An attempt to retrieve inexistent projects was made.

No project is active

An attempt to select a lot without having selected a project was made.

Non existent lots

An attempt to retrieve inexistent lots was made.

No lot is active

An attempt to select a wafer without having selected a lot was made.

Non existent wafers

An attempt to retrieve inexistent wafers was made.

Invalid number of wafers

The number of wafers was zero when trying to run the wafer map simulation.

Upper distribution is undefined

The upper boundary radial distribution was undfined when trying to run the wafer map simulation.

Lower distribution is undefined

The lower boundary radial distribution was undfined when trying to run the wafer map simulation.

Syntax errors in file. Reading aborted

Syntax error in the distribution file were found.

No function has been drawn

An attempt to show or to store a distribution was made.

No analysis has been retrieved

Either the overlap or alternate options were selected without having retrieved an analysis from the database.

Function aborted

<CR> was typed immediately after asking for the name of the file to be stored, or after asking for text in the hardcopy option.

Either the mean or the standard dev. is zero. Simulation skipped

If either of these values is zero the alpha factor is undefined.

Beta is zero. Simulation aborted

The beta factor was found to be zero.

3.2 SYSTEM DIAGNOSTICS

The following are the messages that can appear as a consequence of a conflict between ALWAYS and the operating system. They appear as

[SYSXX]Message

where XX is the number of the message, and Message is a short legend of the problem. If any of these messages appears

1. check ownership of directories
2. check that the directories are accesible

3. check that the files are readable
4. check that the files are writable
5. check that there is enough memory usage space
6. consult with your system manager for help
7. report them to

Jose Pineda de Gyvez
Eindhoven University of Tech.
Design Automation Group
Room 7.16
The Netherlands
Tel (040)-473373

ALWAYS uses the /tmp directory to write information of the partial maps. It creates a file named "projects" which contains the names of each one of the existing projects for the analysis, the same with a file "lots". The file "wafers" contains the functional yield of each one of the wafers involved in the analysis. The partial wafer maps of each project and of each lot are named as "project_name.pro", "project_name_lot_name.lots".

1. Cannot open the file "projects" in the /tmp directory
2. Cannot open the file "lot" in the /tmp directory
3. Cannot open the file "always.errors"
4. Cannot open the file "wafers" in the /tmp directory
5. Cannot write in the "wafers" file
6. Cannot open the partial composite wafer map for each lot
7. Cannot write the partial composite map of each lot
8. Cannot open the file to store the composite wafer of each project
9. Cannot write the partial composite map of each project
10. Cannot open the analysis file
11. Cannot write in the analysis file
12. Cannot open the simulation file
13. Cannot write in the simulation file
14. Cannot open "always.print"
15. Cannot open "wafers" for reading
16. Cannot read "wafers"
17. Cannot open "projects" or "lots" for reading
18. Cannot read "lots" or wafers
19. Cannot read "lots" or "wafers"
20. Cannot open cluster file
21. Cannot read file for clusters
22. Cannot read composite wafer for cluster analysis
23. Cannot link an active project
24. Cannot create header of project list
25. Cannot store the project name
26. Cannot create header of lot list
27. Cannot link an active lot in the list
28. Cannot store the name of the active lot
29. Cannot create header of the wafer list
30. Cannot link wafer in the wafer list
31. Cannot store the wafer name
32. Cannot create the header for continuous lot selection
33. Cannot link lot in continuous lot selection

34. Cannot store the name of the lot in the continuous lot selection
35. Cannot create the header of the wafer list in continuous selection
36. Cannot link a wafer in continuous selection
37. Cannot open lot directory
38. Cannot open lot directory
39. Cannot create header for coordinate list
40. Cannot link coordinates in the list
41. Cannot allocate partial project map
42. Cannot allocate partial lot map
43. Cannot allocate composite map
44. Cannot allocate map for storage as analysis type
45. Cannot allocate cluster map
46. Insufficient space for frequency distribution analysis
47. Insufficient space for cumulative distribution analysis
48. Insufficient space for analysis storage as analysis type
49. Cannot create space for cluster statistics
50. Cannot allocate cluster map for cluster statistics
51. Cannot allocate header of dead dice list
52. Cannot link dead die in the list
53. Cannot create space for simulation map
54. Cannot create space for storage of radial distribution as analysis type
55. Cannot create space for radial distribution
56. Cannot create space for radial map.
57. Cannot create space for storage of angular distribution as analysis type
58. Cannot create space for angular distribution
59. Cannot create header of displayed files list
60. Cannot link file in displayed files list
61. Cannot store the name of the displayed file
62. Cannot store the name of the simulation file to be displayed
63. Cannot store the name of the distribution file to be displayed
64. Cannot store the name of the analysis file to be displayed
65. Cannot store the name of the project path
66. Cannot store the name of the lot path
67. Cannot create space for statistical analysis
68. Cannot create alternate map for "alternate" or "overlap" options
69. Cannot create space to retrieve a distribution
70. Cannot create space for alternate map simulation
71. Cannot create space for the simulated wafer map
72. Cannot create space for radial map in simulation phase.
73. Cannot create space for radial number of dice during simulation
74. Cannot create space for alternate yield vs. area distribution
75. Cannot create space to retrieve distribution file
76. Cannot allocate space to show the current distribution
77. Cannot allocate space to retrieve the distribution

- (168) Linnartz, J.P.M.G.
SPATIAL DISTRIBUTION OF TRAFFIC IN A CELLULAR MOBILE DATA NETWORK.
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- (169) Vinck, A.J. and Pineda de Gyvez, K.A. Post
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